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Absence of the enhanced intra-4f transition cross section at 1.5 μm of Er\(^{3+}\) in Si-rich SiO\(_2\)

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We present measurements of the optical absorption cross section of the \(^{4}I_{15/2} \rightarrow ^{4}I_{13/2}\) transition at 1.5 μm of Er\(^{3+}\) ions embedded in SiO\(_2\) and Si-rich oxide, using cavity ringdown spectroscopy on thin films. The peak absorption cross section for Er\(^{3+}\) embedded in Si-rich oxide (10 at. % excess Si) was found to be \((8 \pm 2) \times 10^{-21} \text{ cm}^2\) at 1536 nm, similar to typical values for Er embedded in SiO\(_2\). The data imply that the silicon nanoclusters incorporated in Si-rich oxide do not enhance the peak cross section of the Er\(^{3+}\) \(^{4}I_{15/2} \rightarrow ^{4}I_{13/2}\) transition by 1-2 orders of magnitude, contrary to what has been reported in earlier work. © 2005 American Institute of Physics. [DOI: 10.1063/1.1949720]

Erbium-doped Si-rich oxide (SRO:Er) is an optical gain medium in which Er\(^{3+}\) ions, exhibiting an intra-4f transition at 1.5 μm, are surrounded by silicon nanoclusters that serve as broadband sensitizers.\(^{1-3}\) A sensitizer coupled to an Er\(^{3+}\) ion absorbs light at a cross section several orders of magnitude larger than Er, and then transfers its energy to the Er\(^{3+}\) ion. Sensitizers have the potential to enable optical amplification at 1.5 μm using low-cost light-emitting diodes in top-pumping configuration, instead of a waveguide-coupled laser tuned to an Er transition.

In addition to the sensitization effect, which is of great technological interest, it has been reported that silicon nanoclusters would enhance the absorption and emission cross sections of the \(^{4}I_{15/2} \rightarrow ^{4}I_{13/2}\) transition at 1.5 μm of Er\(^{3+}\) embedded in SiO\(_2\) by 1-2 orders of magnitude.\(^{4,5}\) This presumed enhancement was derived from optical absorption spectroscopy in linear waveguides,\(^{2}\) and it has been invoked to explain the high signal enhancement in SRO:Er linear amplifiers.\(^{5}\) The enhanced emission cross section has also been used as an input parameter in a model describing the gain characteristics of SRO:Er amplifiers.\(^{6}\)

If true, the cross section enhancement would have a broad impact on Er amplifier and laser technology as it implies an enhancement of the optical gain coefficient by the same 1-2 orders of magnitude. Thus more compact devices would be possible using SRO:Er.

Both reported cross-section enhancements are based on indirect measurements, and a direct determination is still lacking. In this letter, we present measurements of the Er\(^{3+}\) absorption cross section in both SRO:Er and SiO\(_2\):Er by cavity ringdown spectroscopy (CRDS) on thin films,\(^{7,8}\) which is an approach that does not require estimates on the overlap between an optical mode and the erbium profile as in earlier work. From the data it is concluded that the earlier reported 1-2 orders of magnitude enhancement of the cross section of the Er\(^{3+}\) \(^{4}I_{15/2} \rightarrow ^{4}I_{13/2}\) transition at 1.5 μm due to silicon nanoclusters is incorrect.

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light intensity inside the cavity upon pulse injection was detected with a photodiode. Individual transients were sampled using a 12 bit, 100 MHz data acquisition system.

Figure 1 shows cavity ringdown transients detected at 1536 nm for both an SRO:Er sample that was annealed at 800 °C and a bare quartz substrate. After the first microsecond, the transients exhibit a single-exponential behavior of which the rate is determined by the intrinsic cavity loss and the loss generated by the sample placed in the cavity. The ringdown time for SRO:Er (3 μs) is significantly shorter than for quartz (8 μs) due to the stronger extinction of the SRO:Er sample. The single-exponential parts of individual transients were fitted with a standard weighted linear regression technique to extract the ringdown time. Reported values of the optical loss per pass, which includes both scattering and absorption contributions, have been corrected for the empty cavity response and were deduced from averages of the ringdown time over 100 laser shots at every wavelength.

Figure 2 shows the optical loss spectra for SRO:Er and SiO₂:Er determined in this way. Every optical loss spectrum shows a characteristic Er³⁺ absorption spectrum superimposed on a background that is decreasing with wavelength, which is attributed to loss processes not related to Er such as scattering. Repeated measurements after sample realignment gave reproducible results for both peak shape and magnitude, as well as for the decreasing background trend, with some variations in background level. We attribute the latter to variations in both alignment and sample quality.

The estimates of the background losses indicated in Fig. 2 (dashed lines) are based on a qualitative comparison with absorption spectra derived by PL spectroscopy using McCumber theory, as is illustrated in Fig. 3. Figure 3(a) shows a PL spectrum for SRO:Er (annealed at 800 °C) taken at room temperature. The absorption spectral shape derived from this spectrum is shown in Fig. 3(b), together with the corresponding absorption spectrum derived from the optical loss data shown in Fig. 2 by subtraction of the background loss (dashed line). The spectral resemblance between the CRDS-based spectrum and the normalized PL-based spectrum validates the estimate of the background loss.

The important feature shown in Fig. 2 is that, for all three samples, the Er absorption is very similar over the entire wavelength range (within 20%). The Er³⁺ 4I_{13/2} → 4I_{15/2} absorption cross section is thus found to be similar for SiO₂:Er and SRO:Er annealed at either 800 or 1000 °C. Here, it is assumed that all Er ions are in the 3+ valence state, which is justified by the fact that no other valences of Er are reported for a variety of hosts. In addition, X-ray absorption spectroscopy of the Er 3d⁹4f⁰ → 3d⁹4f¹² transitions for Er-doped silicon has shown no evidence of other Er valence states.

The Er³⁺ 4I_{15/2} → 4I_{13/2} absorption cross section for SRO:Er can directly be obtained from Fig. 3(b) by dividing the Er absorption by the Er areal density. This procedure yields a peak absorption cross section, which is related to the maximum gain coefficient for SRO:Er amplifiers, of (8.2 ± 2) × 10⁻²¹ cm² at 1536 nm, where the error bar is determined mainly by the uncertainty in the background level of the absorption measured. This result is close to typical values obtained for Er embedded in glasses: (4.8–7.0) × 10⁻²¹ cm², confirming that silicon nanoclusters do not enhance the cross section of the Er³⁺ 4I_{15/2} → 4I_{13/2} transition by
1-2 orders of magnitude. Note that the cross section in SRO:Er is expected to be 10%–20% larger than in SiO$_2$:Er due to the higher refractive index of the heterogeneous SRO, but the limited signal-to-noise ratio of the SiO$_2$:Er sample does not allow one to resolve this difference from the performed measurements.

For the determination of the Er$^{3+}$ transition at 1.5 $\mu$m in both SRO:Er and SiO$_2$:Er by cavity ringdown spectroscopy on thin films, proving that this is a suitable technique for the determination of rare-earth absorption cross sections. The peak absorption cross section for SRO:Er was found to be $(8 \pm 2) \times 10^{-21}$ cm$^2$, which is identical (within 20%) to the measured cross section for SiO$_2$:Er, and which is a typical value for Er embedded in glasses. This result is in disagreement with earlier reported cross sections enhancements for SRO:Er. The conclusion affects modeling of the gain characteristics of SRO:Er materials that use the presumed enhanced cross section as an input parameter.$^6$

Finally, we speculate on the apparent discrepancy between the cross section for SRO:Er derived here, and the much larger values claimed in earlier work. Kik’s tenfold enhanced cross-section claim$^7$ was based on a calculation that involved an estimated overlap between the optical waveguide mode and the Er profile. Possibly, this overlap was underestimated. As CRDS does not require estimates on modal overlap in order to determine the absorption cross section, the method presented in the current work provides more reliable results. The reported near-hundredfold cross section enhancement derived from gain characteristics of SRO:Er linear amplifiers by Han et al.$^5$ remains puzzling. In any case, such an enhancement is inconsistent with the Er luminescence lifetime of 8 ms reported in the same paper: according to the Füchtbauer-Ladenburg equation,$^11$ the reported Er emission cross section of $(2 \pm 0.5) \times 10^{-19}$ cm$^2$ would correspond to a radiative lifetime of $\sim 0.3$ ms.

In conclusion, we have measured the optical absorption cross section of the Er$^{3+}$ transition at 1.5 $\mu$m in both SRO:Er and SiO$_2$:Er by cavity ringdown spectroscopy on thin films, proving that this is a suitable technique for the determination of rare-earth absorption cross sections.